



**MMST5551** 

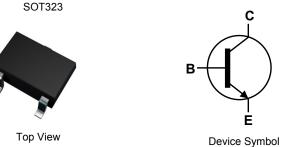
#### **180V NPN SMALL SIGNAL TRANSISTOR IN SOT323**

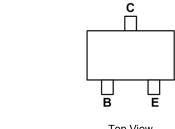
#### Features

- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST5401
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (approximate)





Top View Pin-Out

### Ordering Information (Notes 4 & 5)

Device	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel
MMST5551-7-F	AEC-Q101	K4N	7	8	3,000
MMST5551Q-7-F	Automotive	K4N	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

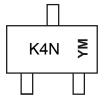
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



K4N = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: A = 2013) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Ke
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Year	2010		2011	2012		2013	2014		2015	2016		2017
Code	Х		Y	Z		А	В		С	D		E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Continuous Collector Current	Ι <sub>C</sub>	200	mA

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	PD	200	mW
Thermal Resistance, Junction to Ambient (Note 6)		R <sub>0JA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 to +150	٥°	

# ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)			•	•	÷
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	180	_	V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	160		V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	6.0	—	V	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	50	nA μA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0 V <sub>CB</sub> = 120V, I <sub>E</sub> = 0, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	50	nA	V <sub>EB</sub> = 4.0V, I <sub>C</sub> = 0
ON CHARACTERISTICS (Note 8)			•	•	÷
DC Current Gain	h <sub>FE</sub>	80 80 30	 250 	_	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.15 0.20	V	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	1.0	V	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Cobo	—	6.0	pF	$V_{CB}$ = -10V, f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	50	250	_	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE}$ = 5.0V, I <sub>C</sub> = 200µA, R <sub>S</sub> =1.0Ω, f = 1.0kHz

Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

Refer to JEDEC specification JESD22-A114 and JESD22-A115.

8. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



T<sub>A</sub> = 25°C

1,000

T<sub>A</sub> = -50°C `||||

100

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Fig. 2, Collector Emitter Saturation Voltage

vs. Collector Current

<del>11</del>11

T<sub>A</sub> = 25°C

10

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Fig. 4, Base Emitter Voltage

vs. Collector Current

= 150°C Τ<sub>A</sub>

100

 $T_A = -50^{\circ}C$ 

# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

0.15

0.14

0.05

0.04

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3 0.2

0.1

V<sub>BE(ON)</sub>, BASE EMITTER VOLTAGE (V)

1

∨<sub>CE</sub> = 5∨

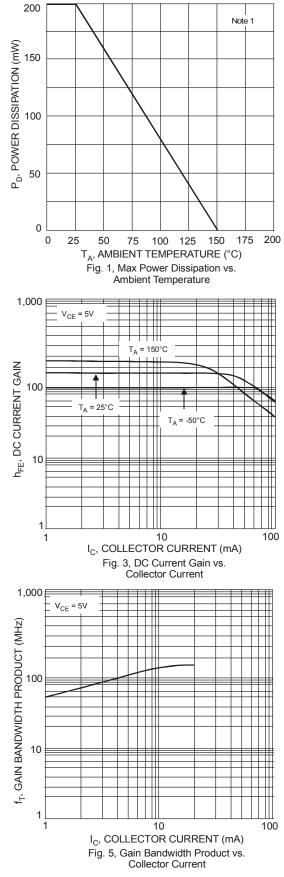
I<sub>C</sub> I<sub>B</sub>

= 10

T<sub>A</sub> = 150°C

10

1



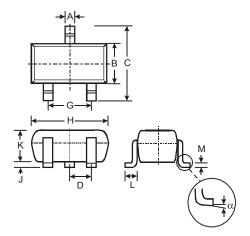






# **Package Outline Dimensions**

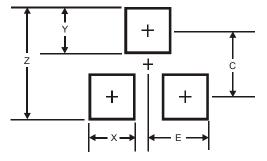
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT323						
Dim	Min	Мах	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	-	-	0.65				
G	1.20	1.40	1.30				
н	1.80	2.20	2.15				
<b>ر</b>	0.0	0.10	0.05				
κ	0.90	1.00	1.00				
L	0.25	0.40	0.30				
М	0.10	0.18	0.11				
α	0°	8°	-				
All	Dimens	ions in	mm				

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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